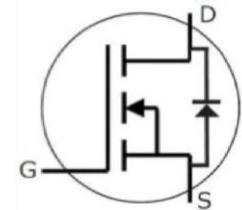
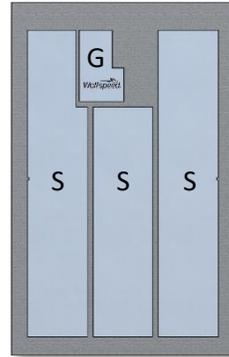


# CPM3-1200-0016A

## Wolfspeed SiC Gen 3 MOSFET

### Description

This is the Wolfspeed's 3rd generation of high performance silicon carbide MOSFET in a packageless bare die format to be implemented into any custom module design. The high blocking voltage with low on-resistance, high speed switching with low capacitance make this MOSFET ideal for high frequency switching application including solar inverters and eVTOL.



Package Types: Bare Die  
PN's: CPM3-1200-0016A

### Features

- 3rd Generation SiC MOSFET
- High blocking voltage with low on-resistance
- High speed switching with low capacitance
- Fast intrinsic diode with low reverse recovery

### Applications

- EV Chargers
- UPS
- Solar Inverters
- SMPS
- eVTOL

### Absolute Maximum Ratings

Stress beyond those listed under absolute maximum ratings may damage the device.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage, across $T_{vj}$	$V_{DS(max)}$	1200	V
Maximum Gate-Source Voltage, Peak Transient Capability	$V_{GS(max)}$	-8/+19	V
Continuous Drain Current, $V_{GS} = 15V$ , assumes die packaged in TO-247 package with $R_{th(j-c)} < 0.28$ K/W	$I_D$	$T_c = 25^\circ C$	115
		$T_c = 100^\circ C$	85
Pulsed Drain Current, $t_p$ limited by $T_{vj(max)}$	$I_{D(pulse)}$	250	A
Virtual Junction and Storage Temperature	$T_{VJ}, T_{stg}$	-55 to +175	$^\circ C$
Maximum Processing Temperature, in non-reactive ambient	$T_{proc}$	325	$^\circ C$

### Recommended Operating Conditions

Parameter	Symbol	Rating	Unit
Recommended Operating Gate - Source Voltage	$V_{GS(op)}$	-4/+15	V

**Electrical Characteristics (T<sub>VJ</sub> = 25 °C)**

Characteristics	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	1200			V	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 100 μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.8	2.5	3.6	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>DS</sub> = 21.23 mA
			2.0		V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>DS</sub> = 21.23 mA, T <sub>VJ</sub> = 175°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		1	32	μA	V <sub>DS</sub> = 1200 V, V <sub>GS</sub> = 0 V
Gate-Source Leakage Current	I <sub>GSS</sub>		10	100	nA	V <sub>GS</sub> = 15 V, V <sub>DS</sub> = 0 V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	11.2	16	20.8	mΩ	V <sub>GS</sub> = 15 V, I <sub>D</sub> = 77.2 A
			28.8			V <sub>GS</sub> = 15 V, I <sub>D</sub> = 77.2 A, T <sub>VJ</sub> = 175°C
Transconductance	g <sub>fs</sub>		53		S	V <sub>DS</sub> = 20 V, I <sub>DS</sub> = 77.2 A
			47			V <sub>DS</sub> = 20 V, I <sub>DS</sub> = 77.2 A, T <sub>VJ</sub> = 175°C
Input Capacitance	C <sub>iss</sub>		6085		pF	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 1000 V f = 100 kHz V <sub>AC</sub> = 25 mV
Output Capacitance	C <sub>oss</sub>		230			
Reverse Transfer Capacitance	C <sub>rss</sub>		13			
C <sub>oss</sub> Stored Energy	E <sub>oss</sub>		120		μJ	V <sub>DS</sub> = 1000 V, f = 100 kHz
Internal Gate Resistance	R <sub>G(int)</sub>		2.6		Ω	f = 1 MHz, V <sub>AC</sub> = 25 mV
Gate to Source Charge	Q <sub>gs</sub>		67		nC	V <sub>DS</sub> = 800 V, V <sub>GS</sub> = -4 V/15 V I <sub>DS</sub> = 77.2 A Per IEC60747-8-4 pg 21
Gate to Drain Charge	Q <sub>gd</sub>		61			
Total Gate Charge	Q <sub>g</sub>		211			

**Reverse Diode Characteristics (T<sub>VJ</sub> = 25 °C)**

Characteristics	Symbol	Typ.	Max.	Unit	Test Conditions
Diode Forward Voltage	V <sub>SD</sub>	4.6		V	V <sub>GS</sub> = -4 V, I <sub>SD</sub> = 38.6 A
		4.2		V	V <sub>GS</sub> = -4 V, I <sub>SD</sub> = 38.6 A, T <sub>VJ</sub> = 175 °C
Reverse Recovery Time	t <sub>rr</sub>	30		ns	V <sub>GS</sub> = -4 V, I <sub>SD</sub> = 77.2 A, V <sub>R</sub> = 800 V dif/dt = 4720 A/μs, T <sub>VJ</sub> = 175 °C
Reverse Recovery Charge	Q <sub>rr</sub>	1238		nC	
Peak Reverse Recovery Current	I <sub>rrm</sub>	59		A	



### Typical Performance

All the graphs are based on a die placed in a TO-247-4L package.

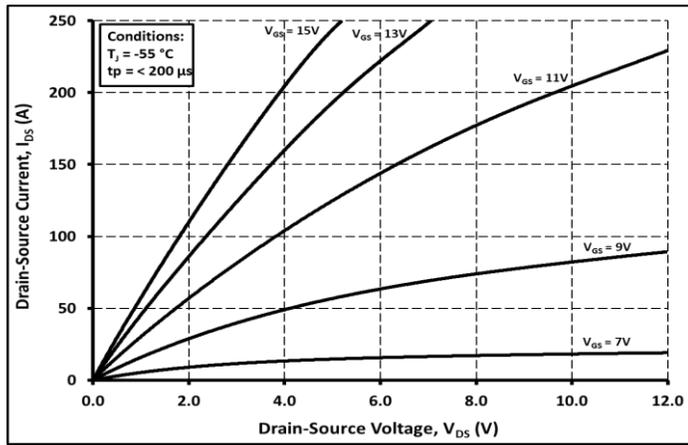


Figure 1.

Output Characteristics  $T_{vj} = -55\text{ }^\circ\text{C}$

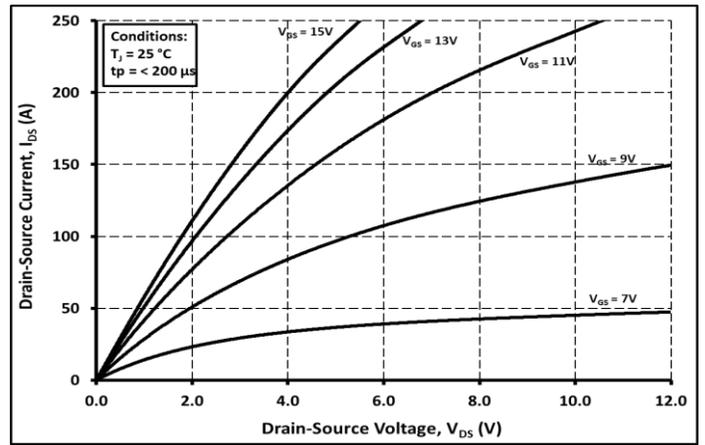


Figure 2.

Output Characteristics  $T_{vj} = 25\text{ }^\circ\text{C}$

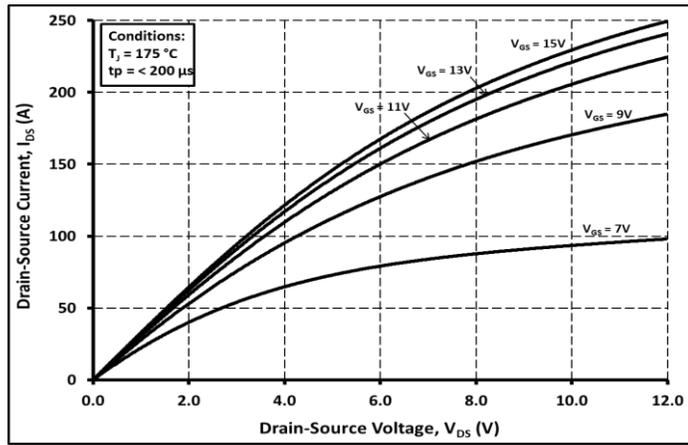


Figure 3.

Output Characteristics  $T_{vj} = 175\text{ }^\circ\text{C}$

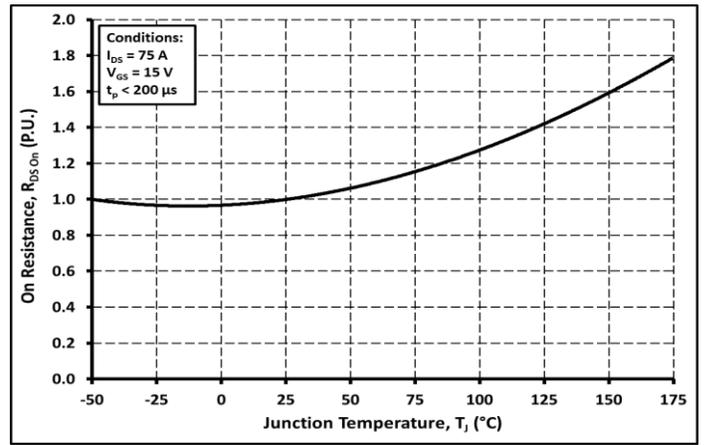


Figure 4.

Normalized On-Resistance vs. Temperature

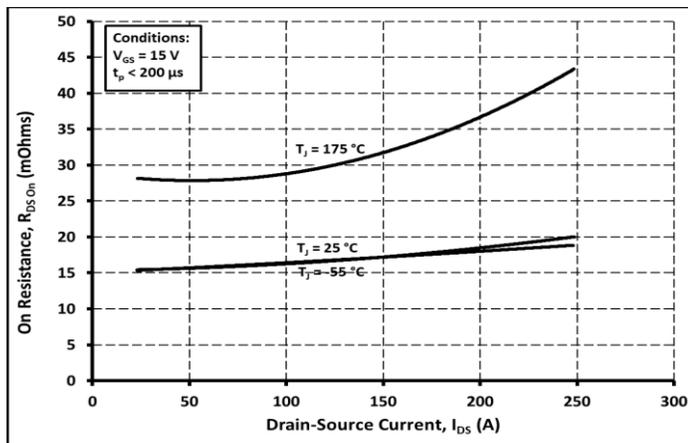


Figure 5.

On-Resistance vs. Drain Current For Various Temperatures

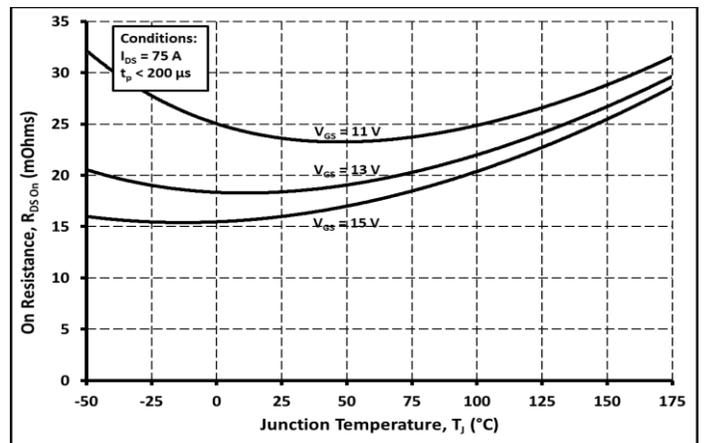


Figure 6.

On-Resistance vs. Temperature For Various Gate Voltages



### Typical Performance

All the graphs are based on a die placed in a TO-247-4L package.

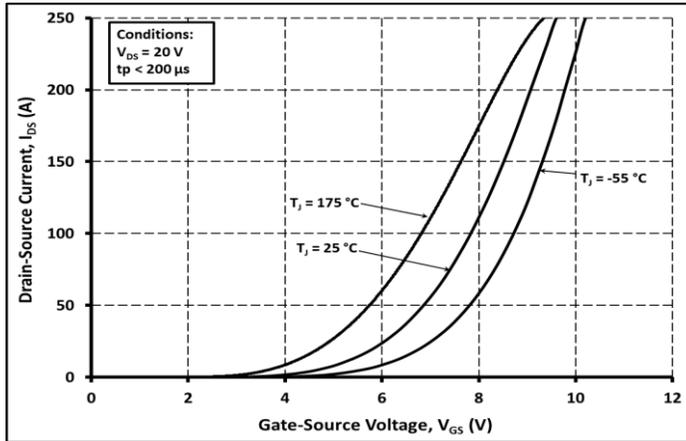


Figure 7.

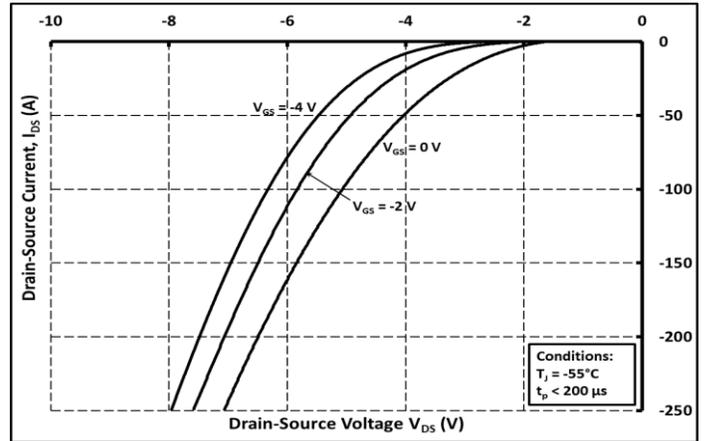


Figure 8.

Transfer Characteristic For Various Junction Temperatures

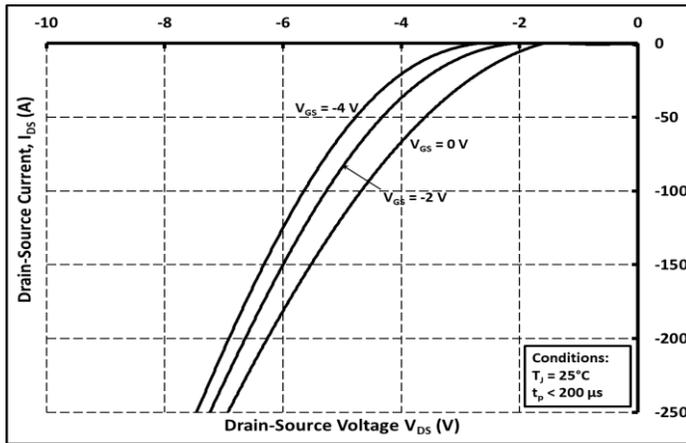


Figure 9.

Body Diode Characteristic at  $T_{vj} = -55\text{ }^{\circ}\text{C}$

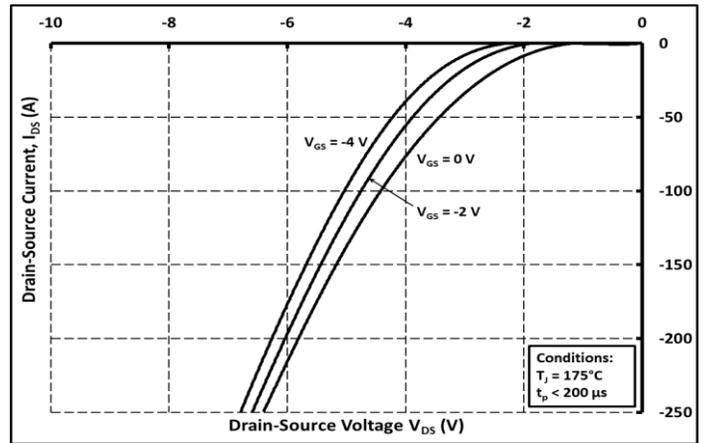


Figure 10.

Body Diode Characteristic at  $T_{vj} = 25\text{ }^{\circ}\text{C}$

Body Diode Characteristic at  $T_{vj} = 175\text{ }^{\circ}\text{C}$

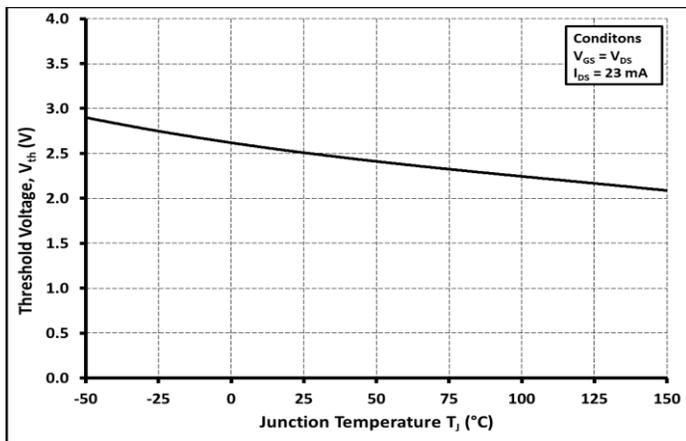


Figure 11.

Threshold Voltage vs. Temperature

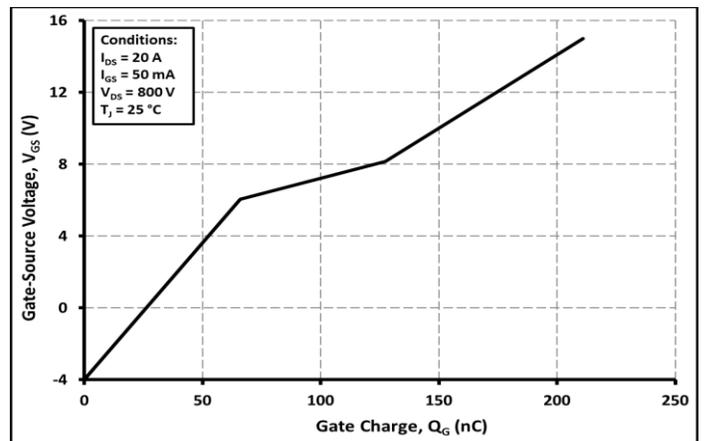


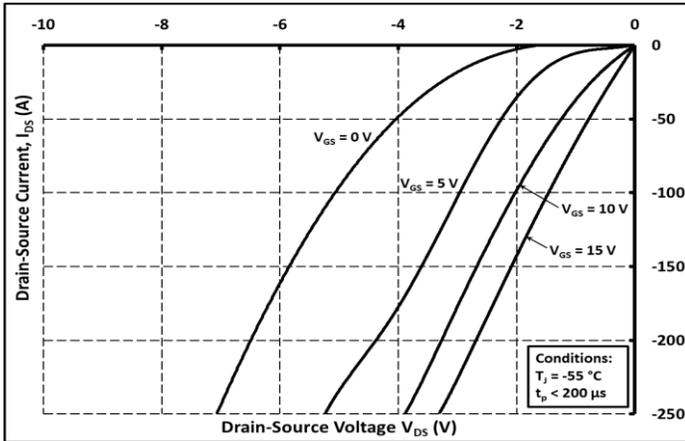
Figure 12.

Gate Charge Characteristics



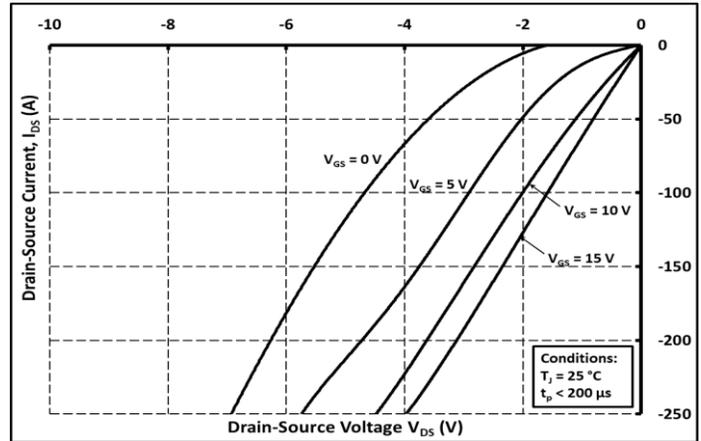
**Typical Performance**

All the graphs are based on a die placed in a TO-247-4L package.



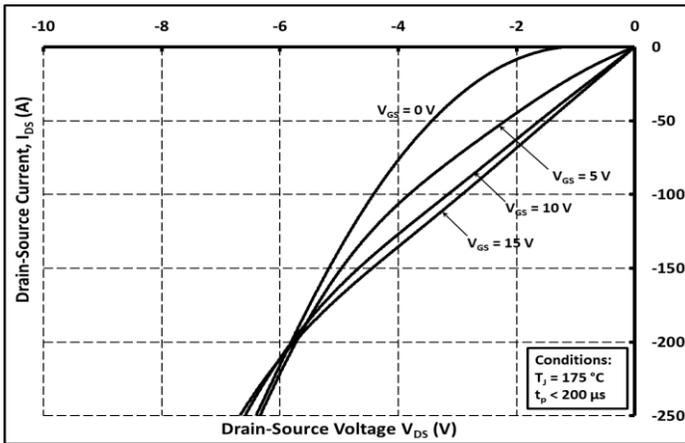
**Figure 13.**

3rd Quadrant Characteristic at  $T_{vj} = -55\text{ }^{\circ}\text{C}$



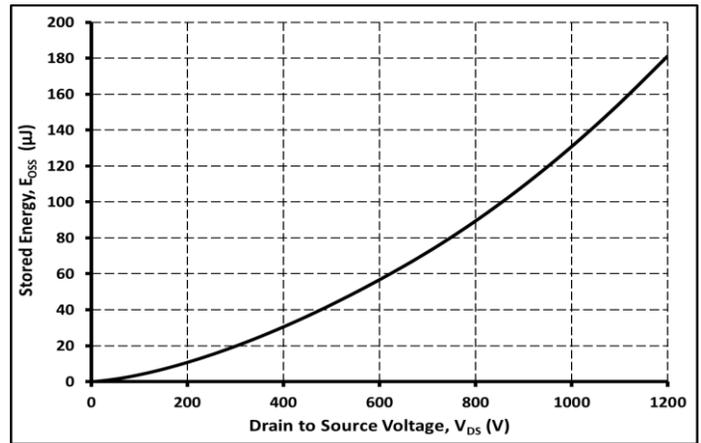
**Figure 14.**

3rd Quadrant Characteristic at  $T_{vj} = 25\text{ }^{\circ}\text{C}$



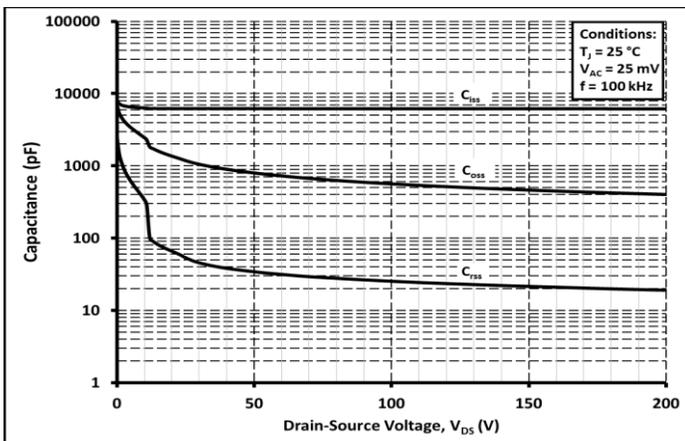
**Figure 15.**

3rd Quadrant Characteristic at  $T_{vj} = 175\text{ }^{\circ}\text{C}$



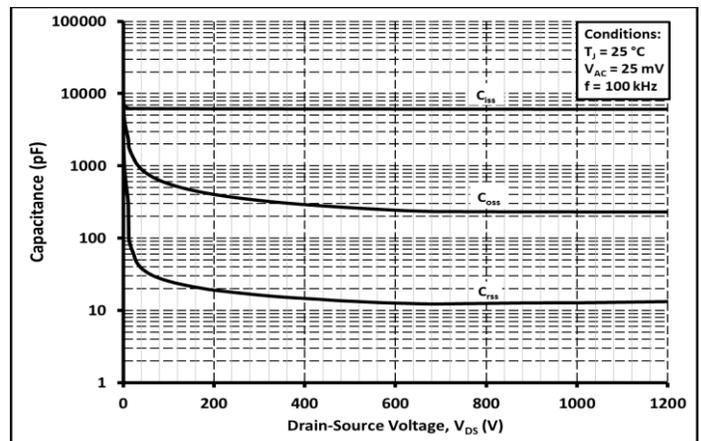
**Figure 16.**

Output Capacitor Stored Energy



**Figure 17.**

Capacitances vs. Drain-Source Voltage (0-200V)



**Figure 18.**

Capacitances vs. Drain-Source Voltage (0-1200V)



## Product Ordering Information

Order Number	Description	Package
CPM3-1200-0013A-FY6	SIC MOSFET G3 IND 1200V/16mO UV MLT	Bare Die Product
CPM3-1200-0013A-GQ8	SIC MOSFET G3 IND 1200V/16mO UV MVF	Bare Die Product

## Revision History

Revision History	Date of Change	Brief Summary
-	04/04/2019	Initial Release
1	01/09/2020	<ul style="list-style-type: none"> <li>Removed test conditions and note section from the Maximum Ratings Table</li> <li>Updated description for all the parameters in the Maximum Ratings Table</li> <li>Updated footnotes</li> <li>Temperature note removed and embedded into every test condition</li> <li>Updated test conditions for gate threshold voltage, drain-source on-state resistance, transconductance, gate to source charge, gate to drain charge, total gate charge, diode forward voltage, reverse recovery time, reverse recovery charge and peak reverse recovery current</li> <li>Updated typical values for continuous drain current, zero gate voltage drain current, gate-source leakage current, drain-source on-state resistance, transconductance, input capacitance, reverse transfer capacitance, Coss stored energy, gate to source charge, gate to drain charge, total gate charge, reverse recovery time and reverse recovery charge</li> <li>All junction temperatures changed to virtual junction temperatures</li> </ul>
2	01/06/2021	<ul style="list-style-type: none"> <li>Update <math>R_{th(j-c)}</math> from 0.4 K/W to 0.28 K/W</li> </ul>
3	7/30/2023	<ul style="list-style-type: none"> <li>Document format updated</li> </ul>



## Notes & Disclaimer

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